

<b>Notice of References Cited</b>	Application/Control No. 10/807,235	Applicant(s)/Patent Under Reexamination SAKAI ET AL.	
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**U.S. PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-			
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	C	US-			
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**FOREIGN PATENT DOCUMENTS**

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**NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	T. Kanashima et al., "Preparation by Pulsed Laser Deposition and Characterization of ZrO <sub>2</sub> , HfO <sub>2</sub> and PrOx Thin Films for High-k Gate Insulator", June 2002, Proceedings of the 13th IEEE International Symposium on Applications of ferroelectrics, pages 199-202
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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.